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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-30EPH03PBF</u>

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Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of VS-30EPH03PBF - DIODE GEN PURP 300V 30A TO247AC

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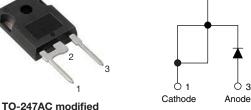




Vishay Semiconductors

Ultrafast Rectifier, 30 A FRED Pt®





Base common

cathode Q 2

FEATURES

- · Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- · Designed and qualified according to JEDEC®-JESD 47







DESCRIPTION / APPLICATION

300 V series are the state of the art ultrafast recovery rectifiers designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

PRODUCT SUMMARY	
Package	TO-247AC modified (2 pins)
I _{F(AV)}	30 A
V _R	300 V
V _F at I _F	0.9 V
t _{rr} typ.	See Recovery table
T _J max.	175 °C
Diode variation	Single die

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V_{RRM}		300	V		
Average rectified forward current	I _{F(AV)}	T _C = 143 °C	30	^		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	300	А		
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	300	-	-			
Forward voltage	V _F	I _F = 30 A	-	1.08	1.25	V		
		$I_F = 30 \text{ A}, T_J = 125 ^{\circ}\text{C}$	-	0.9	1.00			
December 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1		V _R = V _R rated	-	0.05	60			
Reverse leakage current	I _R	$T_J = 125 ^{\circ}C$, $V_R = V_R$ rated	-	280	600	μΑ		
Junction capacitance	C _T	V _R = 300 V	-	90	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	1	3.5	-	nH		



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time	t _{rr}	I _F = 1.0 A, dI _F /dt =	$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	55		
		T _J = 25 °C	I _F = 30 A dI _F /dt = - 200 A/μs V _R = 200 V	-	38	-	ns	
		T _J = 125 °C		-	52	-		
Peak recovery current	I _{RRM}	T _J = 25 °C		-	2.8	-	Δ.	
		T _J = 125 °C		-	7.3	-	Α	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	53	-	0	
		T _J = 125 °C		-	190	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	0.5	0.9		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.4	-		
Weight			-	6.0	-	g	
vveigni			-	0.22	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC modified		30EF	PH03		



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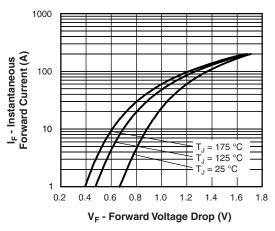


Fig. 1 - Typical Forward Voltage Drop Characteristics

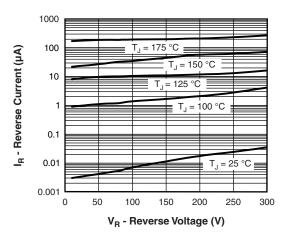


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

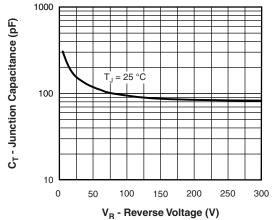


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

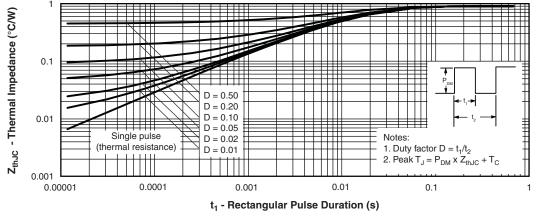


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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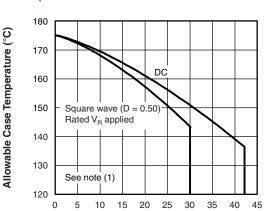
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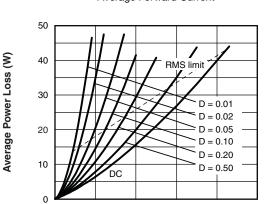
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I_{F(AV)} - Average Forward Current (A) Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current



I_{F(AV)} - Average Forward Current (A) Fig. 6 - Forward Power Loss Characteristics

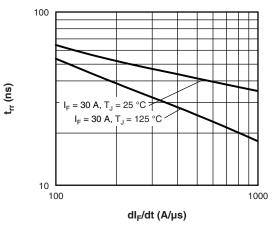


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

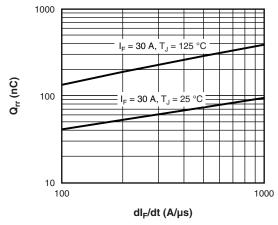


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = Inverse power loss = $V_{R1} \times I_{R}$ (1 - D); I_{R} at V_{R1} = Rated V_{R}

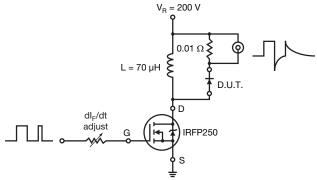


Fig. 9 - Reverse Recovery Parameter Test Circuit

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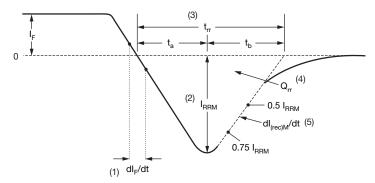
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- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

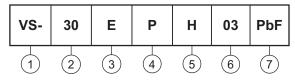
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- Current rating (30 = 30 A)
- Circuit configuration:
 - E = single diode
- Package:
 - P = TO-247AC modified
- H = hyperfast recovery
- Voltage rating (03 = 300 V)
- Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-30EPH03PbF	25	500	Antistatic plastic tube				
VS-30EPH03-N3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95541			
Dort marking information	TO-247AC modified PbF	www.vishay.com/doc?95255			
Part marking information	TO-247AC modified -N3	www.vishay.com/doc?95442			

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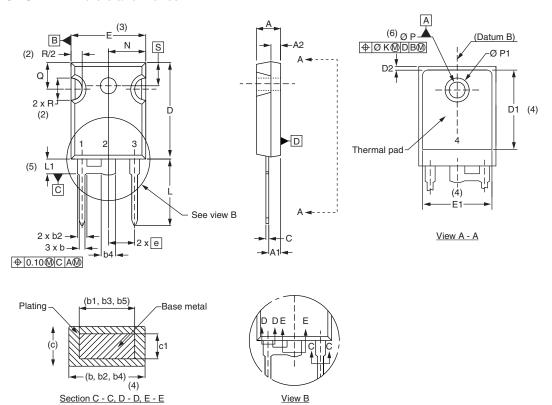


Outline Dimensions

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TO-247 - 50 mils L/F modified

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	MILLIMETERS		INCHES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.17	1.37	0.046	0.054	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIM	MILLIMETERS		INCHES	
STWIDGE	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.35	0.020	0.053	
Е	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	•	
е	5.46	BSC	0.215 BSC		
ØK	0.2	254	0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
N	7.62 BSC		0.3		
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51	BSC	0.217 BSC		

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q

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